

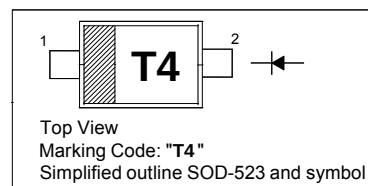
Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- Ultra-small surface mount package
- For general purpose switching applications
- High conductance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	125	mA
Forward Continuous Current	I_{FM}	250	mA
Non-repetitive Peak Forward Surge Current at $t = 1\ \mu\text{s}$ at $t = 100\ \text{ms}$	I_{FSM}	2 1	A
Power Dissipation	P_{tot}	150	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating Temperature Range	T_j	- 65 to + 150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\ \mu\text{A}$	$V_{(BR)R}$	75	-	V
Forward Voltage at $I_F = 1\ \text{mA}$ at $I_F = 10\ \text{mA}$ at $I_F = 50\ \text{mA}$ at $I_F = 150\ \text{mA}$	V_F	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at $V_R = 75\ \text{V}$ at $V_R = 20\ \text{V}$ at $V_R = 75\ \text{V}$, $T_J = 150^\circ\text{C}$ at $V_R = 25\ \text{V}$, $T_J = 150^\circ\text{C}$	I_R	- - - -	1 25 50 30	μA nA μA μA
Total Capacitance at $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R$, $I_F = I_R = 10\ \text{mA}$, $R_L = 100\ \Omega$	t_{rr}	-	4	ns

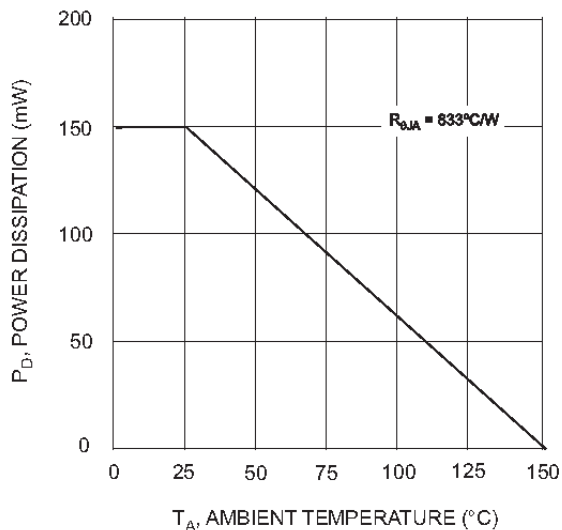


Fig. 1 Derating Curve

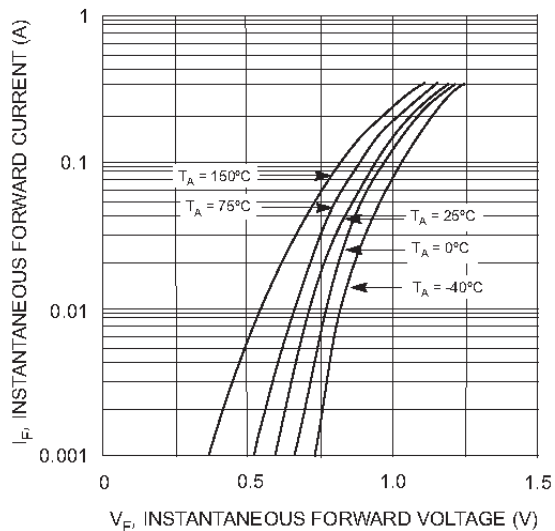


Fig. 2 Forward Characteristics

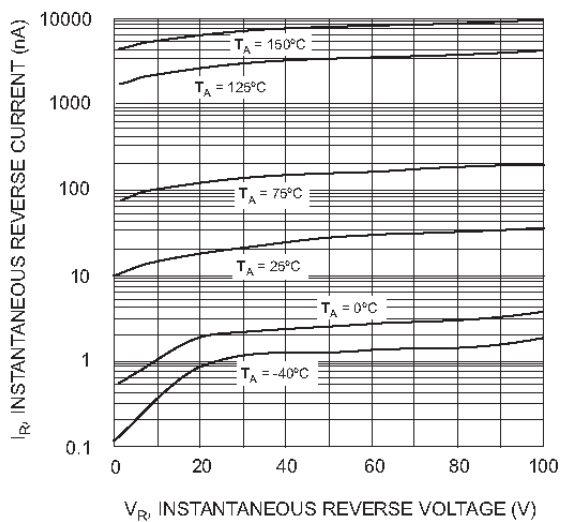


Fig. 3 Typical Reverse Characteristics

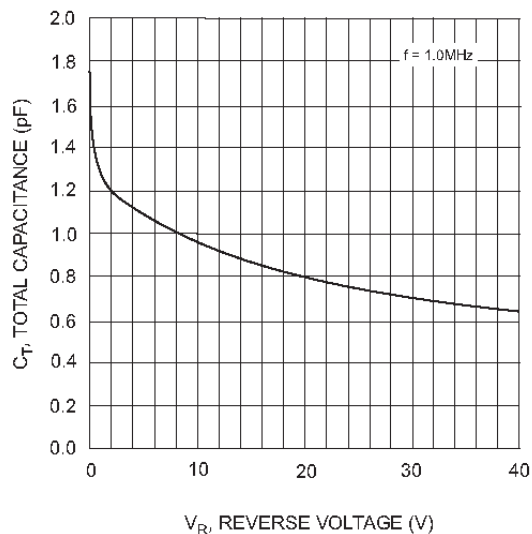
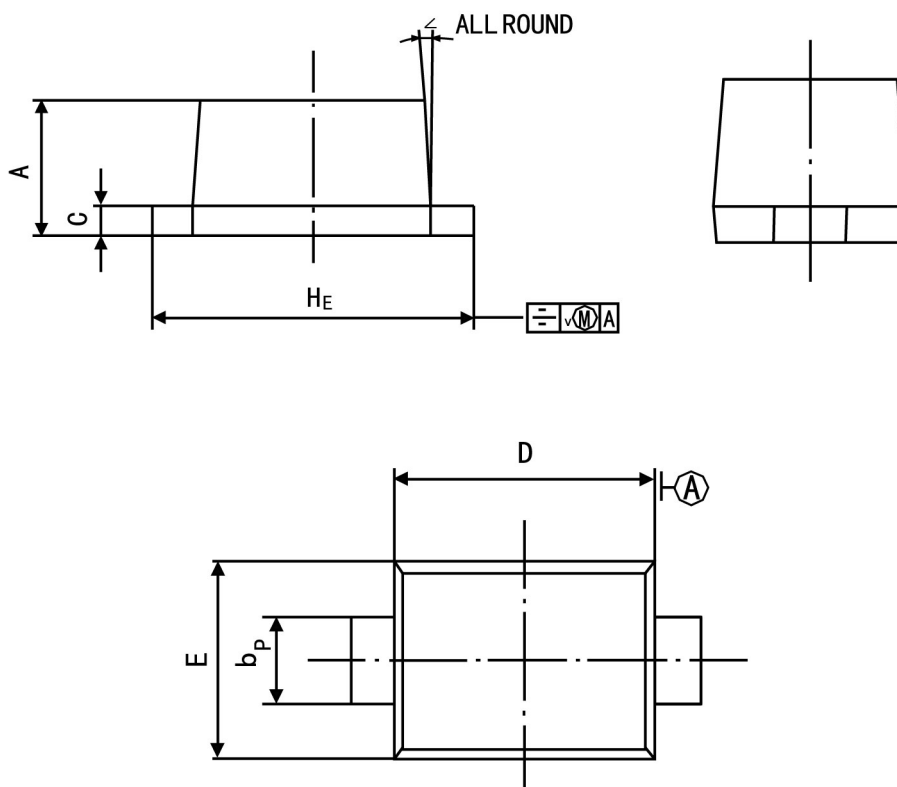


Fig. 4 Typical Capacitance vs. Reverse Voltage

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
bp	0.30	0.40
C	0.100	0.14
D	1.15	1.25
E	0.75	0.85
HE	1.50	1.70
V	—	0.10
∠	—	5°